

2SD1847

Silicon NPN Triple-Diffused Planar Type

Horizontal Deflection Output

■ Features

- Damper diode built-in
- Minimizes external component counts and simplifies circuitry
- High breakdown voltage, high reliability
- High speed switching
- Wide area of safety operation (ASO)
- "Full Pack" package for simplified mounting on a heat sink with one screw

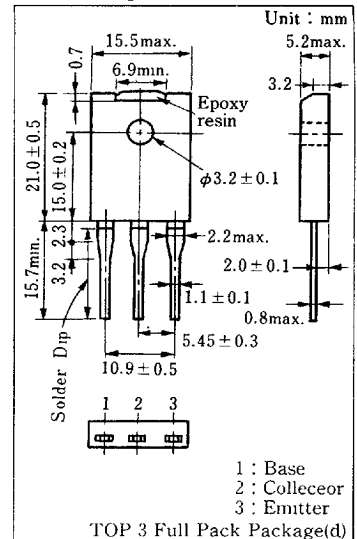
■ Absolute Maximum Ratings (T_c=25°C)

Item	Symbol	Value	Unit	
Collector-base voltage	V _{CB0}	1500	V	
Collector-emitter voltage	V _{CE5}	1500	V	
	V _{CEO}	700	V	
Emitter-base voltage	V _{EBO}	7	V	
Peak collector current	I _{CP}	15	A	
Collector current	I _C	5	A	
Base current	I _B	2	A	
Collector power dissipation	P _C	T _c = 25°C	100	W
		T _a = 25°C	3	
Junction temperature	T _J	150	°C	
Storage temperature	T _{stg}	-55 ~ +150	°C	

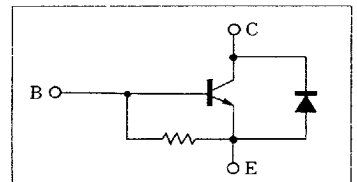
■ Electrical Characteristics (T_c=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector cutoff current	I _{CBO}	V _{CB} = 750V, I _E = 0			10	μA
		V _{CB} = 1500V, I _E = 0			1	mA
Emitter-base voltage	V _{EBO}	I _E = 500mA, I _C = 0	7			V
DC current gain	h _{FE}	V _{CE} = 5V, I _C = 1A	5		25	
		V _{CE} = 10V, I _C = 4A	4			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 4A, I _B = 1A			8	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 4A, I _B = 1A			1.5	V
Transition frequency	f _T	V _{CE} = 10V, I _C = 1A, f = 0.5MHz		2		MHz
Storage time (L load)	t _{stg}	I _C = 4A, I _{B1} = 1A			9	μs
Collector current fall time (L load)	t _f	I _{B2} = -1A, L _{leak} = 5μH			0.8	μs
Storage time (R load)	t _{stg}	I _C = 4A, I _{B1} = 1A		1.5		μs
Collector current fall time (R load)	t _f	I _{B2} = -2A, V _{CC} = 200V		0.2		μs
Diode forward voltage	V _F	I _C = -5A, I _B = 0			2.3	V

■ Package Dimensions



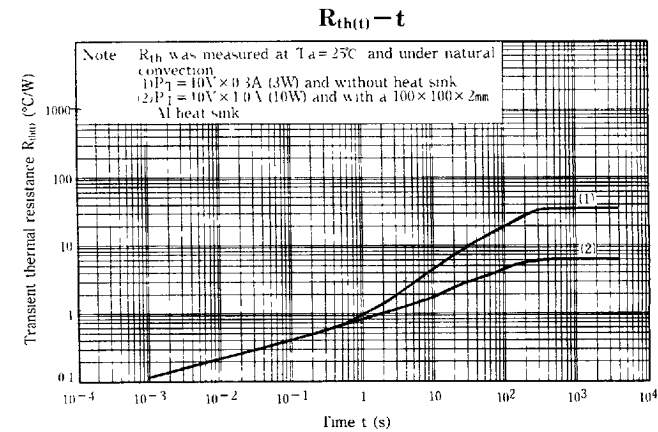
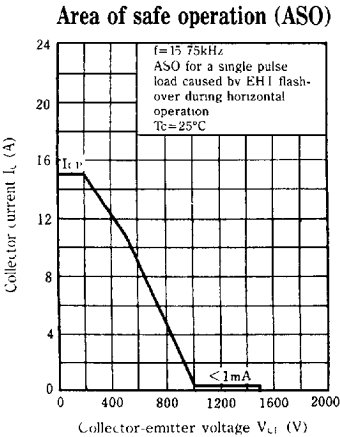
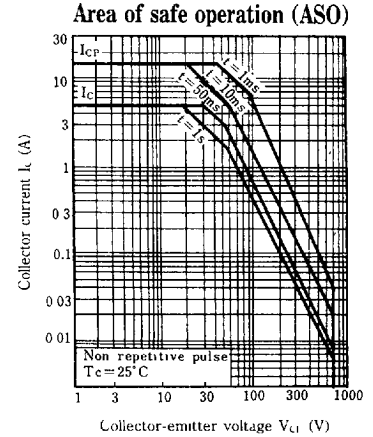
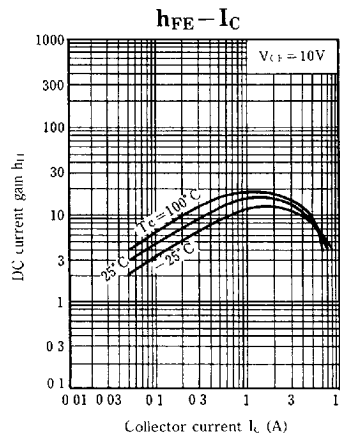
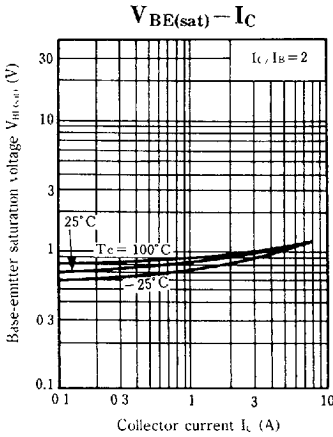
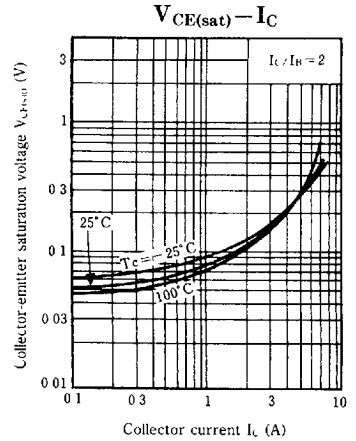
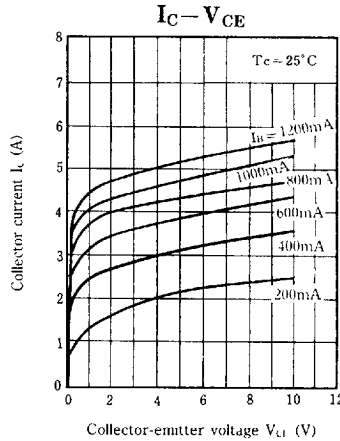
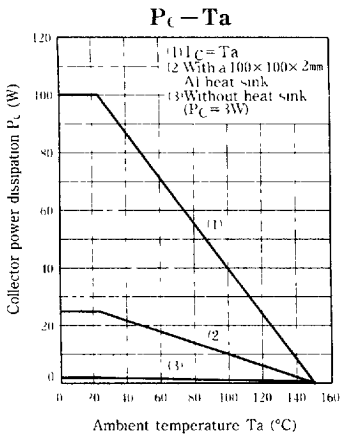
■ Inner Circuit



Panasonic

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